Application No.: 10/591,449 Reply Under 37 C.F.R. § 1.116

Expedited Procedure Technology Center: 1700

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LIST OF CURRENT CLAIMS

1. (Currently Amended) A rare earth oxide superconductor comprising:

a metal substrate;

an intermediate layer formed on the surface of the metal substrate by sequentially

disposing:

a first intermediate cerium-based oxide layer comprising cerium and one

or more solid solution formation elements, selected from the group consisting of

Y, Nd, Sm, Gd, Eu, Yb, Ho, Tm, Dy, La and Er, which are capable of forming a

solid solution with cerium and selected from the group consisting of Y, Nd, Sm,

Gd, Eu, Yb, Ho, Tm, Dy, La and Er, and

a second intermediate cerium-based oxide layer, different from the first

intermediate cerium-based oxide layer and comprising cerium and one or more

charge compensation elements capable of compensating for a charge mismatch

attributable to a difference between the electron valences of respective ions of

cerium and the solid solution formation element, and selected from the group

consisting of Bi, Nb, Sb, Ta and V, wherein the total of the solid solution

formation element and the charge compensation element in the intermediate

layers is 5 to 60 mol% in terms of the metal content; and

a rare earth oxide superconductive layer formed on the intermediate layer

and having a critical temperature (Tc) of 85-88° K.

2 - 10. (Canceled)

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11. (Previously Presented) The rare earth oxide superconductor according to claim 1,

wherein the metal substrate is a biaxially aligned metal substrate.

12. (Currently Amended) A method for producing a rare earth oxide superconductor

comprising the steps of:

applying a mixed solution, on the surface of a metal substrate, comprising an

organometallic acid salt of cerium and an organometallic acid salt of one or more solid

solution formation elements, selected from the group consisting of Y, Nd, Sm, Gd, Eu,

Yb, Ho, Tm, Dy, La and Er, which are capable of forming a solid solution with cerium

and selected from the group consisting of Y, Nd, Sm, Gd, Eu, Yb, Ho, Tm, Dy, La and

Er, and then preliminarily calcining the same to form a first cerium-based oxide

intermediate layer;

applying a mixed solution, on the first cerium-based oxide intermediate layer,

comprising an organometallic acid salt of cerium and an organometallic acid salt of one

or more of a charge compensation element capable of compensating for a charge

mismatch attributable to a difference between the electron valences of respective ions of

cerium and the solid solution formation element and selected from the group consisting

of Bi, Nb, Sb, Ta and V, to form a second cerium-based oxide intermediate layer,

wherein the total of the solid solution formation element and the charge compensation

element in the intermediate layers is 5 to 60 mol% in terms of the metal content, followed

by a heat treatment in a reducing atmosphere under a pressure ranging from 0.1 Pa to

below atmospheric pressure and a temperature in a range from 900 to 1200°C to form a

cerium-based oxide intermediate layer including the first and second cerium-based oxide

intermediate layers; and then

forming by an MOD method a rare earth oxide superconductive layer on the

intermediate layer.

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13 - 17. (Canceled)

18. (Previously Presented) The method for producing a rare earth oxide superconductor

according to claim 12, wherein the cerium-based oxide intermediate layer is formed by

calcination in a reducing atmosphere under a pressure in a range from 10 to 500 Pa and a

temperature ranging from 950 to 1150°C.

19-26. (Canceled)

27. (Previously Presented) The rare earth oxide according to claim 1 wherein the solid

solution formation element is Gd and the charge compensation element is Nb.

28. (Previously Presented) The method for producing a rare earth oxide superconductor

according to claim 12 wherein the solid solution formation element is Gd and the charge

compensation element is Nb.

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